

Application No. 10/708,936
Technology Center 2813
Amendment dated March 13, 2006
Reply to Office Action of December 13, 2005

Amendments to the Specification:

Please replace paragraph [0020] with the following amended paragraph:¹

Figure 6 shows the result of stripping the field oxide 42 and the remaining regions 32, 34 and 40 of the oxide layers 16 and 18 from both sides of the wafer 10, resulting in the wafer 10 comprising an array of cap die 52. Each cap die 52 comprises a through-hole 48, a recess 50, and a land 54 that completely surrounds the recess 50. The lands 54 subsequently serve as bonding surfaces for the cap wafer 10 when mated and bonded to a device wafer (not shown). When mated with the device wafer, the through-holes 48 can be aligned with bond pads (such as the bond pads 62 of Figure 7) or any other feature on the device wafer to which access is desired. Simultaneously, the recesses 50 are aligned with regions of the device wafer on which elements are present that are desired to be encapsulated (such as the micromachined element 58 of Figure 7). Thereafter, individual device packages (such as the package 64 in

¹ All references to pages and paragraphs in Applicant's electronically-filed application are those inserted by the USPTO authoring software.

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Figure 7) can be sawn from the wafer stack produced by the wafer bonding operation. As known in the art, if the operation of the micromachined element 58 requires or benefits from operating in a vacuum, the cap wafer 10 can be bonded to the device wafer so that each cavity 60 defined by the recesses 50 forms a reference vacuum chamber.